

- ★ Green Device Available
- ★ Super Low Gate Charge
- ★ Excellent CdV/dt effect decline
- ★ Advanced high cell density Trench technology

Product Summary

RoHS

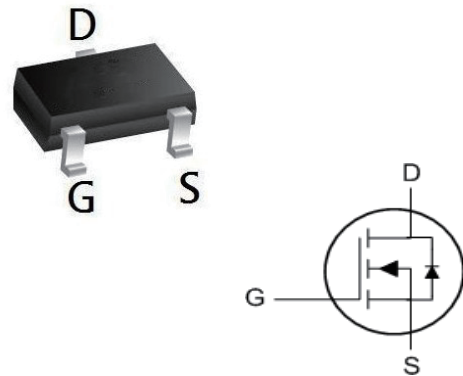
BVDSS	RDS(on)	ID
20V	19mΩ	6.0A

Description

The 2300A is the high cell density trenched N-ch MOSFETs, which provide excellent $R_{DS(on)}$ and efficiency for most of the small power switching and load switch applications.

The 2300A meet the RoHS and Green Product requirement with full function reliability approved.

SOT23 Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	20	V
V_{GS}	Gate-Source Voltage	± 12	V
$I_{D@T_A=25^\circ C}$	Continuous Drain Current, $V_{GS} @ 4.5V^1$	6	A
$I_{D@T_A=70^\circ C}$	Continuous Drain Current, $V_{GS} @ 4.5V^1$	4	A
I_{DM}	Pulsed Drain Current ²	15	A
$P_{D@T_A=25^\circ C}$	Total Power Dissipation ³	1	W
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ C$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ C$

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-Ambient ¹	---	125	$^\circ C/W$
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	---	80	$^\circ C/W$

Electrical Characteristics ($T_J = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
BV_{DS}	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	20	---	---	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance ²	$V_{GS}=4.5V, I_D=3A$	---	19	35	$m\Omega$
		$V_{GS}=2.5V, I_D=2A$	---	35	60	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}, I_D=250\mu A$	0.4	---	1.2	V
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=16V, V_{GS}=0V,$	---	---	1	μA
		$V_{DS}=16V, V_{GS}=0V,$	---	---	5	
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 12V, V_{DS}=0V$	---	---	± 100	nA
g_{fs}	Forward Transconductance	$V_{DS}=5V, I_D=3A$	---	10.5	---	S
Q_g	Total Gate Charge (4.5V)	$V_{DS}=15V, V_{GS}=4.5V,$ $I_D=3A$	---	4.6	---	nC
Q_{gs}	Gate-Source Charge		---	0.7	---	
Q_{gd}	Gate-Drain Charge		---	1.5	---	
$T_{d(on)}$	Turn-On Delay Time	$V_{DD}=10V, V_{GS}=4.5V,$ $R_G=3.3\Omega, I_D=3A$	---	1.6	---	ns
T_r	Rise Time		---	42	---	
$T_{d(off)}$	Turn-Off Delay Time		---	14	---	
T_f	Fall Time		---	7	---	
C_{iss}	Input Capacitance	$V_{DS}=15V, V_{GS}=0V,$ $f=1MHz$	---	310	---	pF
C_{oss}	Output Capacitance		---	49	---	
C_{rss}	Reverse Transfer Capacitance		---	35	---	

Diode Characteristics

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
I_S	Continuous Source Current ^{1,4}	$V_G=V_D=0V$, Force Current	---	---	6	A
V_{SD}	Diode Forward Voltage ²	$V_{GS}=0V, I_S=1A, T_J=25^\circ\text{C}$	---	---	1.2	V

Note :

1.The data tested by surface mounted on a 1 inch² FR-4 board with 20Z copper.

2.The data tested by pulsed , pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$

3.The power dissipation is limited by 150°C junction temperature

4.The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.

Typical Performance Characteristics

Figure1: Output Characteristics

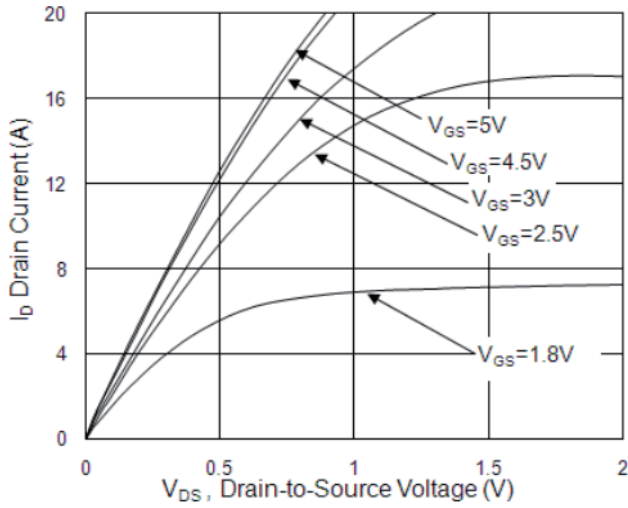


Figure 2: Typical Transfer Characteristics

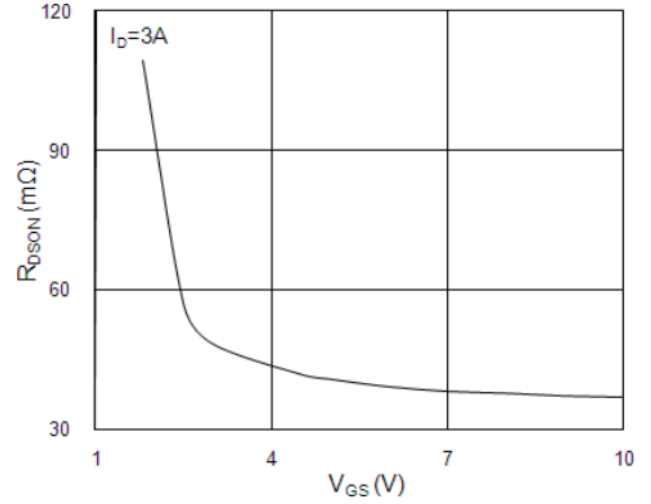


Figure 3: Forward Characteristics of Reverse

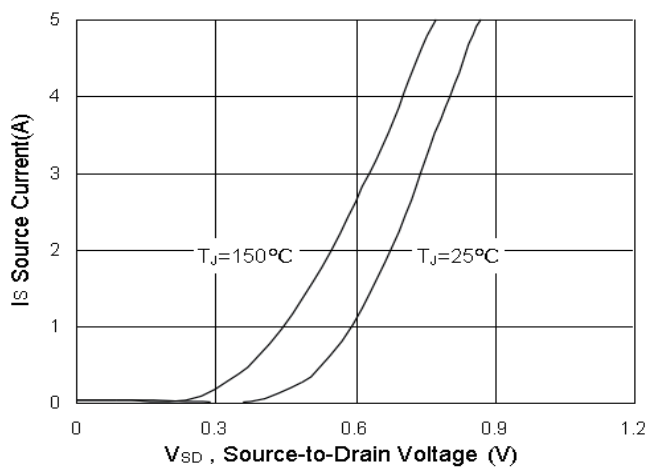


Figure 4: Gate-Charge Characteristics

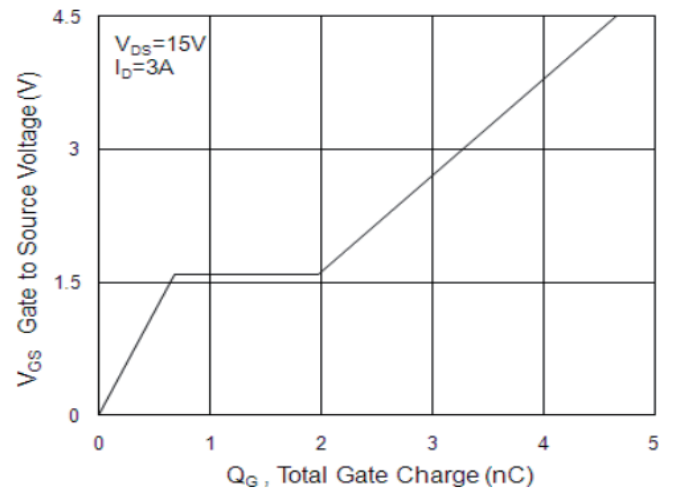


Figure 5: Normalized VGS(th) vs. TJ

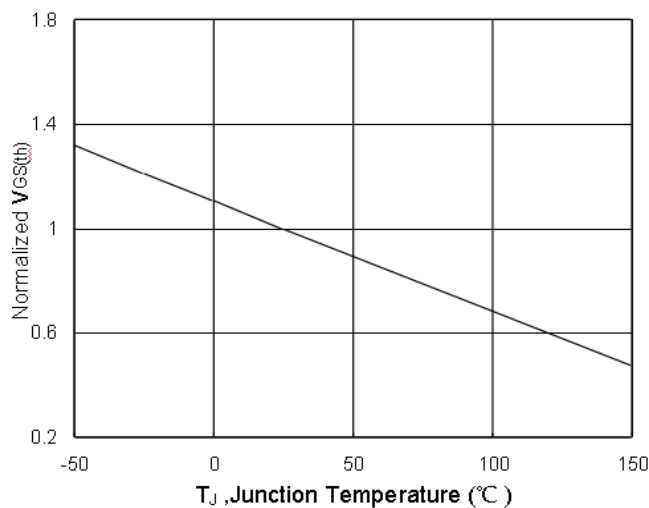
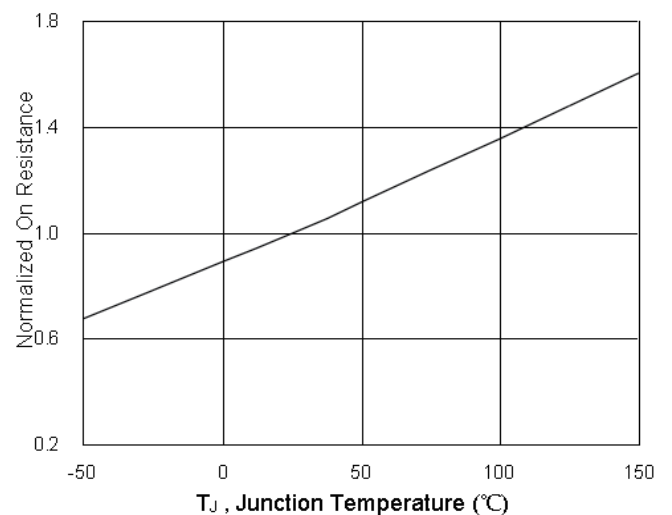


Figure 6: Normalized RDS(on) vs. TJ



Typical Performance Characteristics

Figure 7: Capacitance

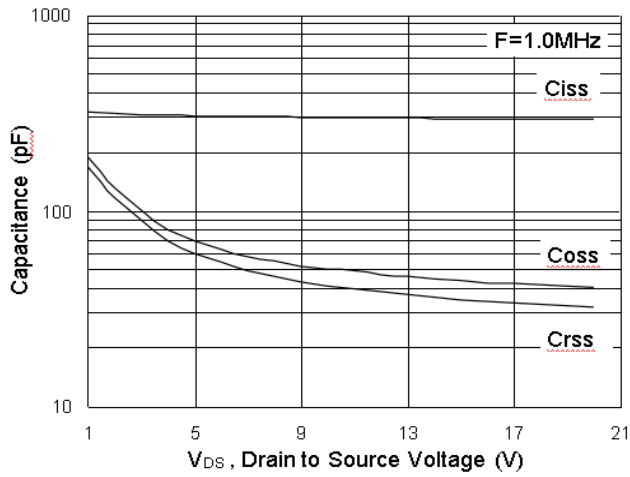


Figure 8: Safe Operating Area

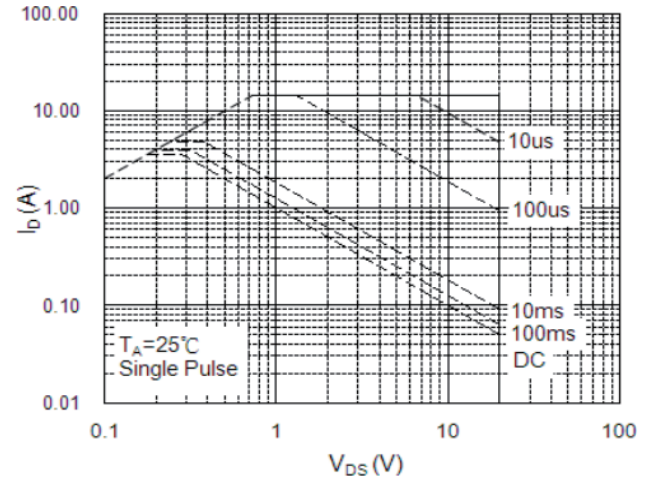


Figure.9: Gate Charge Waveform

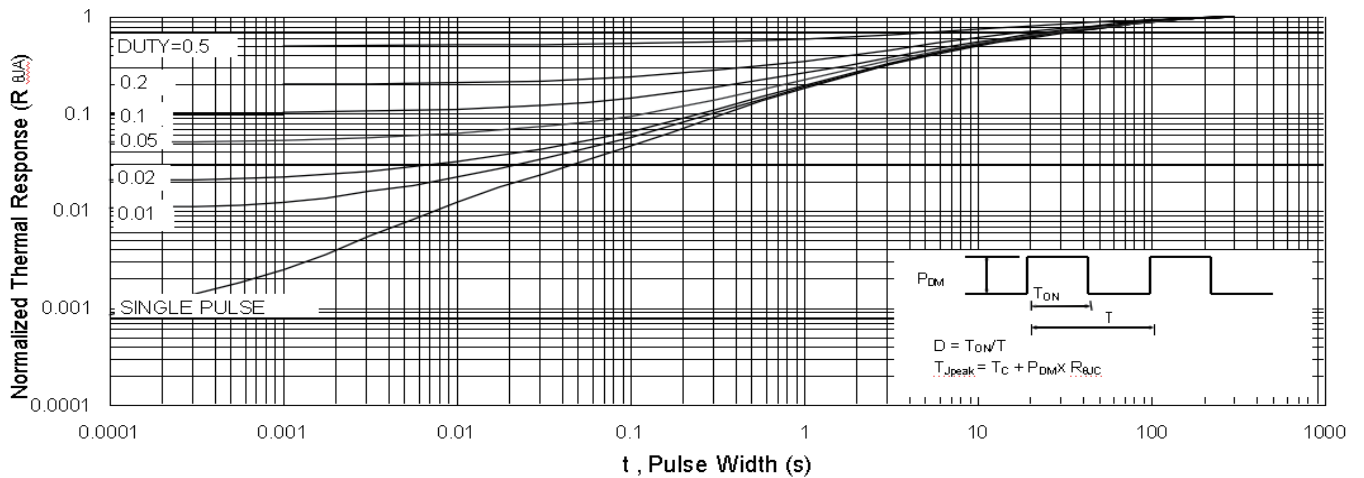


Figure.10: Switching Time Waveform

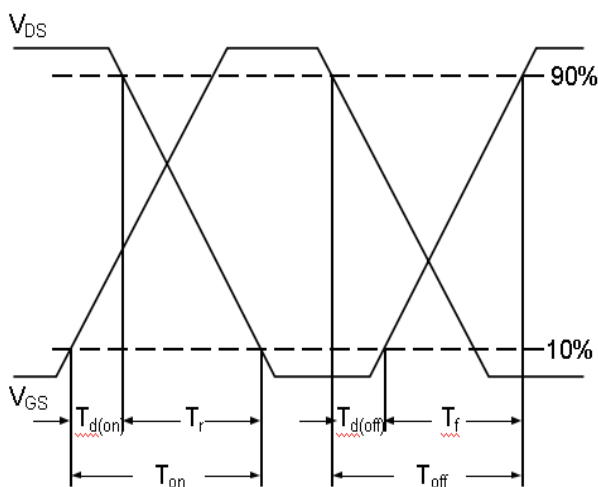
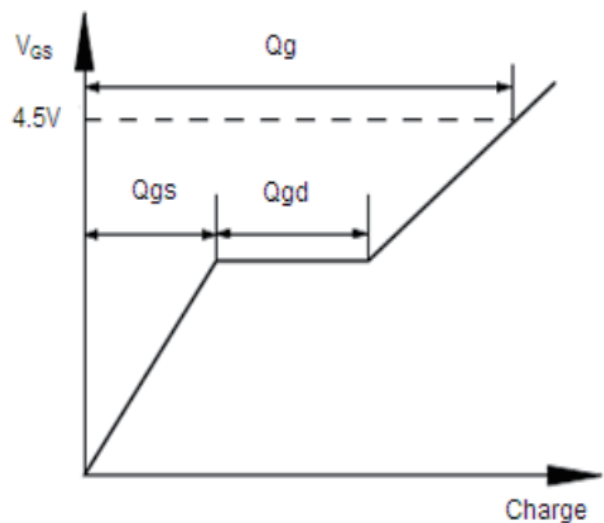
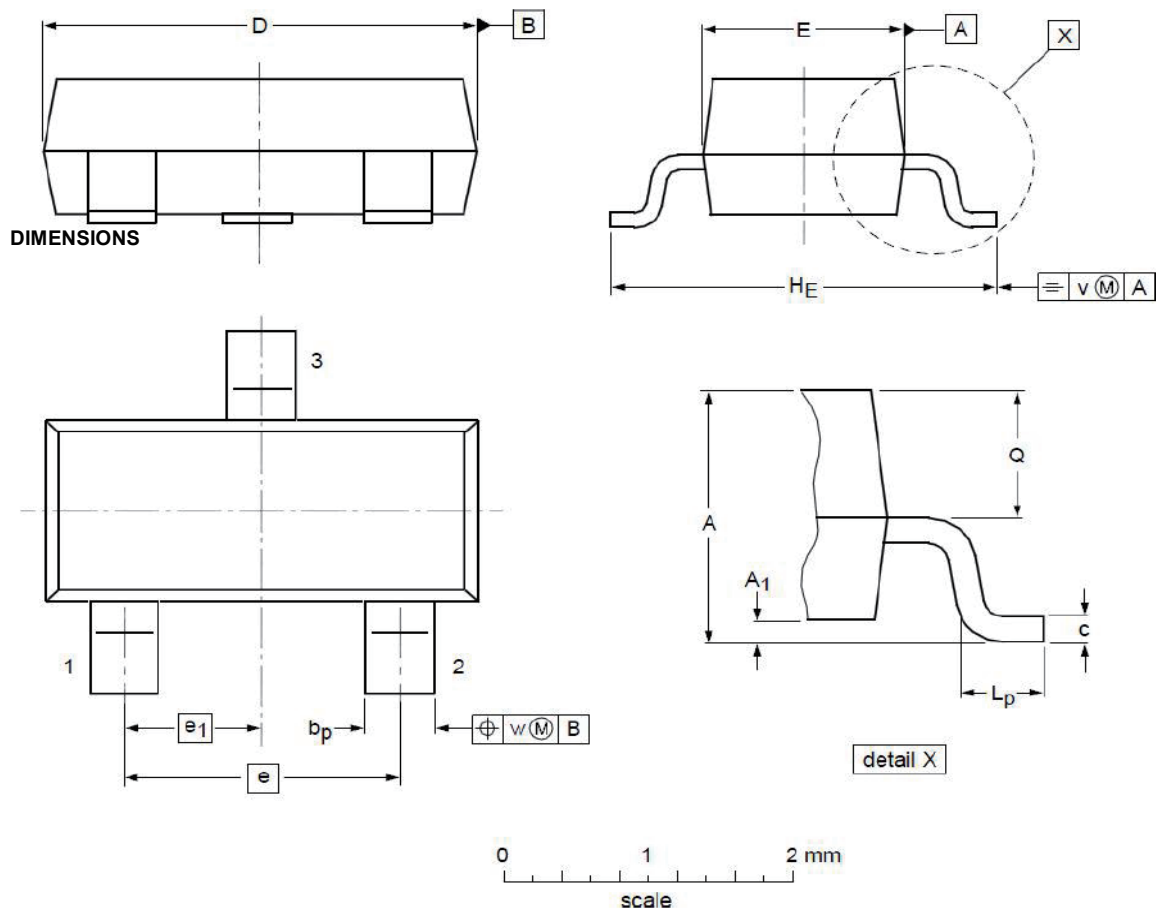


Figure.11: Gate Charge Waveform



SOT23 Mechanical tData



DIMENSIONS (unit : mm)

Symbol	Min	Typ	Max	Symbol	Min	Typ	Max
A	0.9	1.01	1.15	A ₁	0.01	0.05	0.1
b _p	0.3	0.42	0.5	c	0.08	0.13	0.15
D	2.8	2.92	3	E	1.2	1.33	1.4
e	--	1.9	--	e ₁	--	0.95	--
H _E	2.25	2.4	2.55	L _p	0.3	0.42	0.5
Q	0.45	0.49	0.55	v	--	0.2	--
w	--	0.1	--				